UNR5154 (UN5154)

Silicon PNP epitaxial planar type

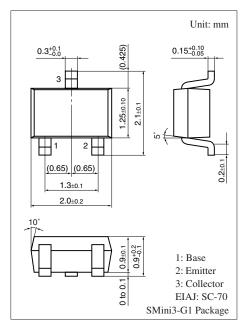
For digital circuits

■ Features

- \bullet High forward current transfer ratio h_{FE}
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts
- S-Mini type package, allowing automatic insertion through tape packing and magazine packing

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-30	V	
Collector-emitter voltage (Base open)	V _{CEO}	-30	V	
Collector current	I_C	-100	mA	
Total power dissipation	P_{T}	150	mW	
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	



Marking Symbol: EV

Internal Connection

$$\begin{array}{c}
R_1 (10 k\Omega) \\
B \circ W \\
R_2 \\
(47 k\Omega)
\end{array}$$

$$\begin{array}{c}
C \\
\end{array}$$

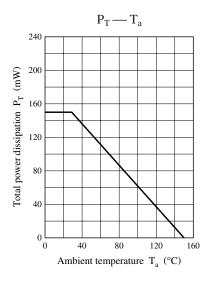
■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

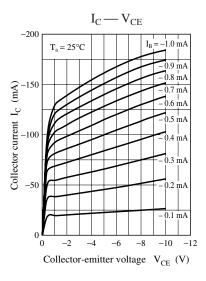
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_{\rm C} = -10 \; \mu \text{A}, \; I_{\rm E} = 0$	-30			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-30			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -30 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -30 \text{ V}, I_{B} = 0$			- 0.5	
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -3 \text{ V}, I_C = 0$			- 0.1	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = -10 \text{ V}, I_{C} = -5 \text{ mA}$	80			_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -50 \text{ mA}, I_B = -0.33 \text{ mA}$		- 0.5	-1.2	V
Output voltage high-level	V_{OH}	$V_{CC} = -5 \text{ V}, V_{B} = -0.5 \text{ V}, R_{L} = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	V_{OL}	$V_{CC} = -5 \text{ V}, V_B = -2.5 \text{ V}, R_L = 1 \text{ k}\Omega$			- 0.2	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz
Input resistance	R_1		-30%	10	+30%	kΩ
Resistance ratio	R_1/R_2			0.213		_

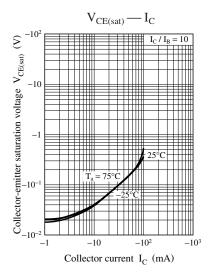
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

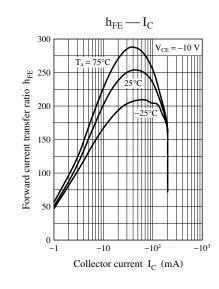
Note) The part number in the parenthesis shows conventional part number.

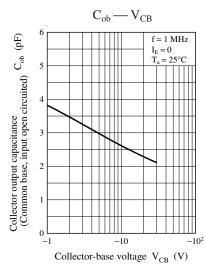
Panasonic

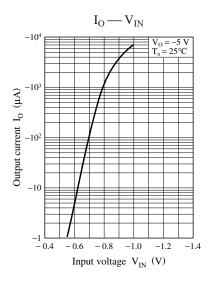


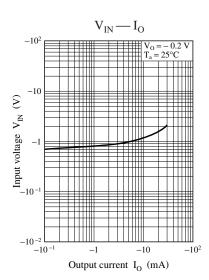












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